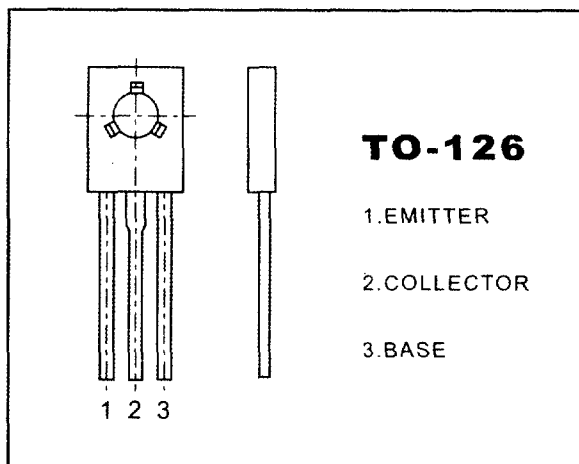


TO-126 Plastic-Encapsulate Transistors

D882 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 1.25W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 3 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 mA, I_B = 0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB} = 40 V, I_E = 0$		1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 30 V, I_B = 0$		1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6 V, I_C = 0$		1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 2 V, I_C = 1 A$	60	400	
	$h_{FE(2)}$	$V_{CE} = 2 V, I_C = 100 mA$	32		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 2 A, I_B = 0.2 A$		0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = 2 A, I_B = 0.2 A$		2	V
Transition frequency	f_T	$V_{CE} = 5 V, I_C = 0.1 A$ $f = 10 MHz$	50		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

Typical Characteristics

D882

